



General Description

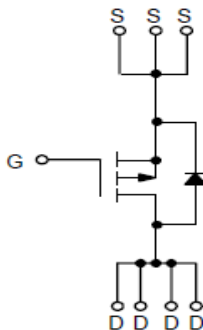
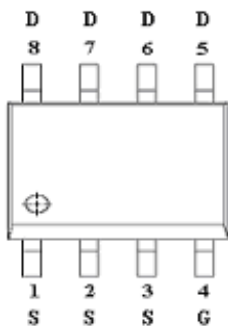
AFP9566W, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- -40V/-5.0A, $R_{DS(ON)} = 80m\Omega @ V_{GS} = -10V$
- -40V/-3.5A, $R_{DS(ON)} = 105m\Omega @ V_{GS} = -4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- SOP-8P package design

Pin Description (SOP-8P)



Application

- Backlight Inverter for LCD Display
- Full Bridge DC/DC Converter
- Load Switch
- CCFL Inverter

Pin Define

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP9566WS8RG	9566W	SOP-8P	Tape & Reel	2500 EA

※ A Lot code

※ B Date code

※ AFP9566WS8RG : 13" Tape & Reel ; Pb- Free ; Halogen- Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	-30	V
Gate –Source Voltage	V _{GSS}	±20	V
Continuous Drain Current(T _J =150°C)	I _D	T _A =25°C	-5.0
		T _A =70°C	-3.5
Pulsed Drain Current	I _{DM}	-15	A
Continuous Source Current(Diode Conduction)	I _S	-2	A
Power Dissipation	P _D	T _A =25°C	2.8
		T _A =70°C	1.8
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	62.5	°C/W

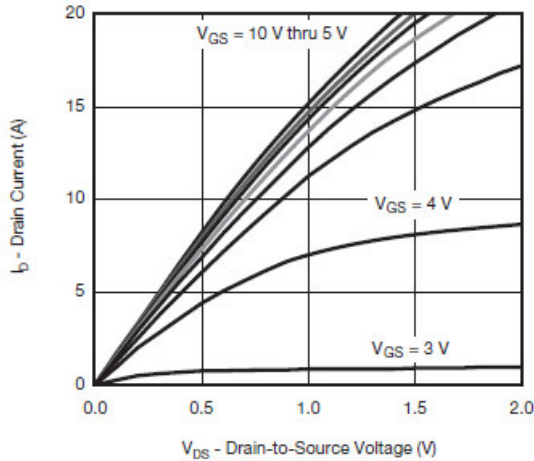
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

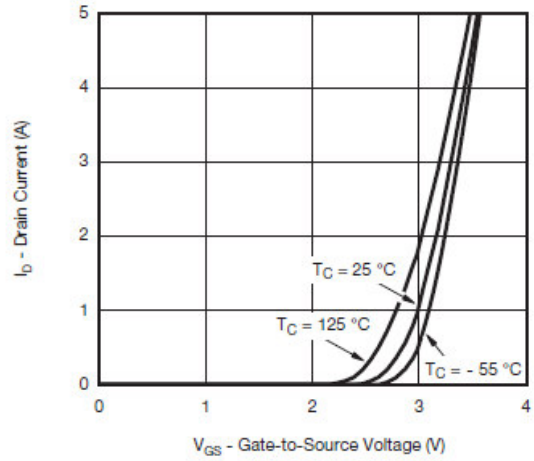
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250uA	-40			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1.0		-2.0	V
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-32V, V _{GS} =0V			-1	uA
		V _{DS} =-32V, V _{GS} =0V T _J =85°C			-30	
On-State Drain Current	I _{D(on)}	V _{DS} ≤ -5V, V _{GS} =-10V	-5			A
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-5.0A		68	80	mΩ
		V _{GS} =-4.5V, I _D =-3.5A		90	105	
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-3.0A		8		S
Diode Forward Voltage	V _{SD}	I _S =-1.25A, V _{GS} =0V		-0.75	-1.3	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =-20V, V _{GS} =-4.5V I _D ≡-3.0A		5	10	nC
Gate-Source Charge	Q _{gs}			1.5		
Gate-Drain Charge	Q _{gd}			2.5		
Input Capacitance	C _{iss}	V _{DS} =-20V, V _{GS} =0V f=1MHz		500		pF
Output Capacitance	C _{oss}			65		
Reverse Transfer Capacitance	C _{rss}			50		
Turn-On Time	t _{d(on)}	V _{DD} =-20V, R _L =8Ω I _D ≡-2.5A, V _{GEN} =-4.5V R _G =1.0Ω		25	50	ns
	t _r			15	30	
Turn-Off Time	t _{d(off)}			10	25	
	t _f			10	25	



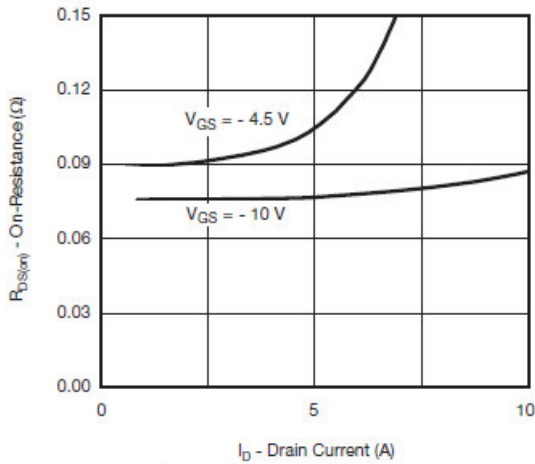
Typical Characteristics



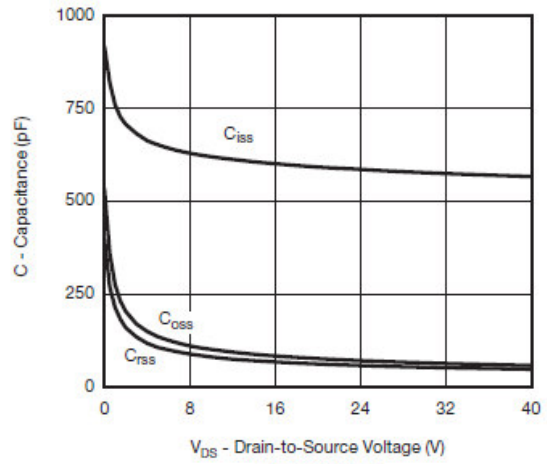
Output Characteristics



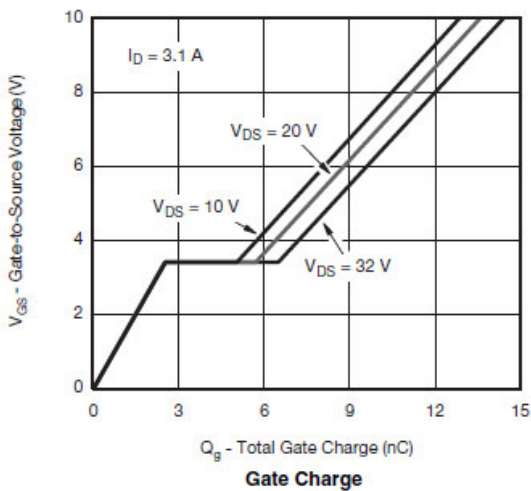
Transfer Characteristics



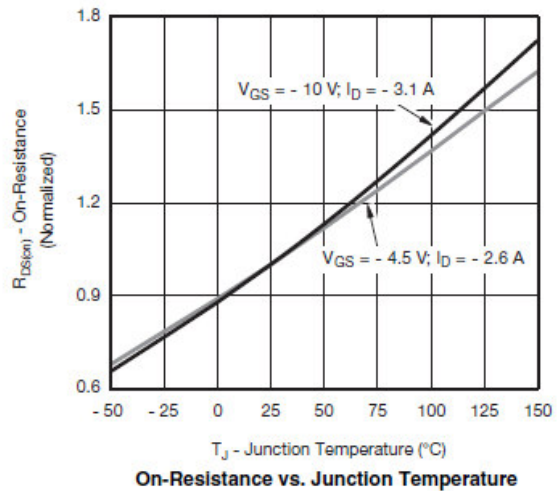
On-Resistance vs. Drain Current



Capacitance



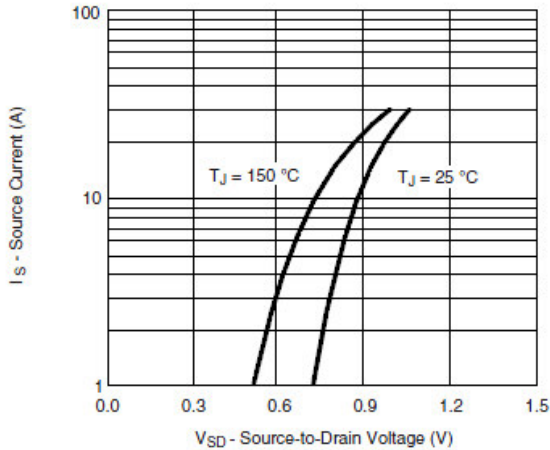
Gate Charge



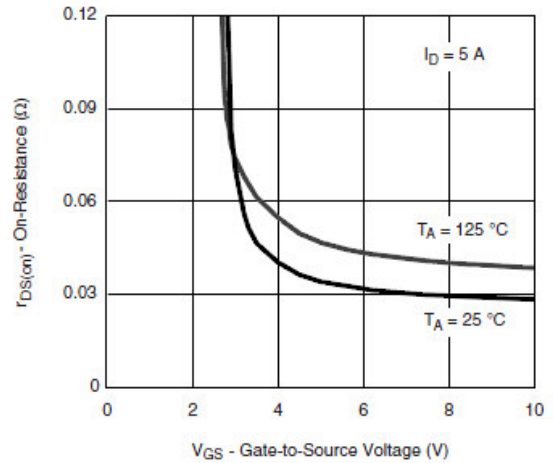
On-Resistance vs. Junction Temperature



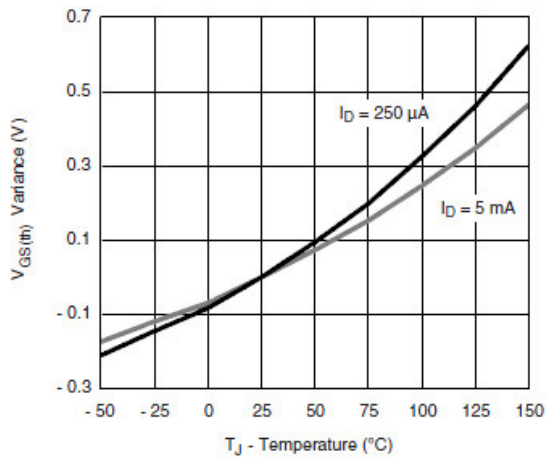
Typical Characteristics



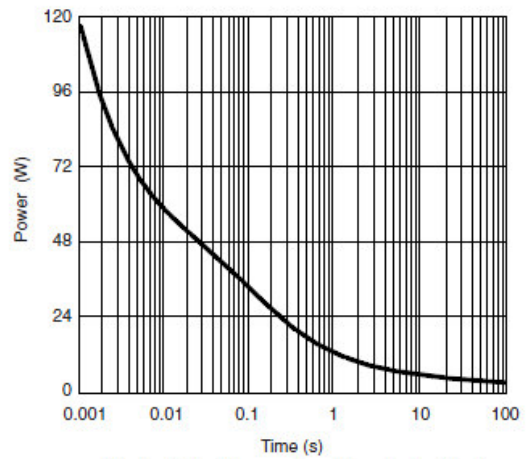
Source-Drain Diode Forward Voltage



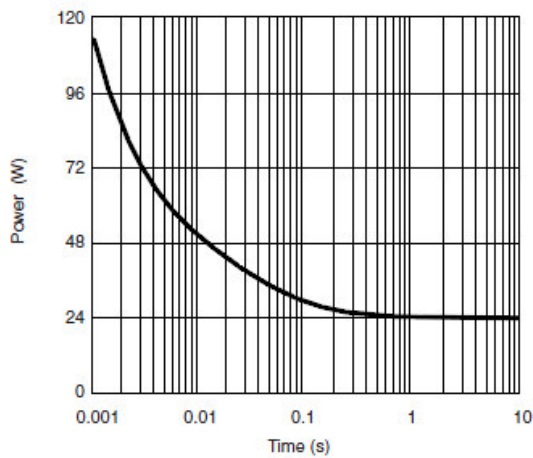
On-Resistance vs. Gate-to-Source Voltage



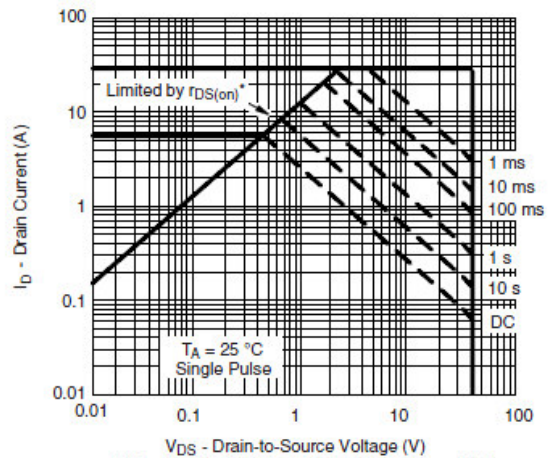
Threshold Voltage



Single Pulse Power, Junction-to-Ambient



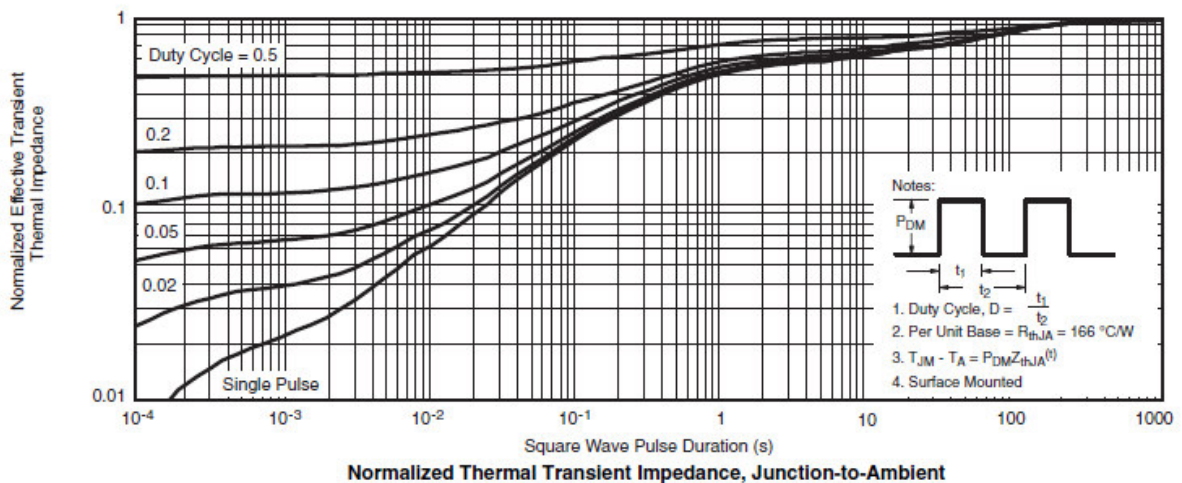
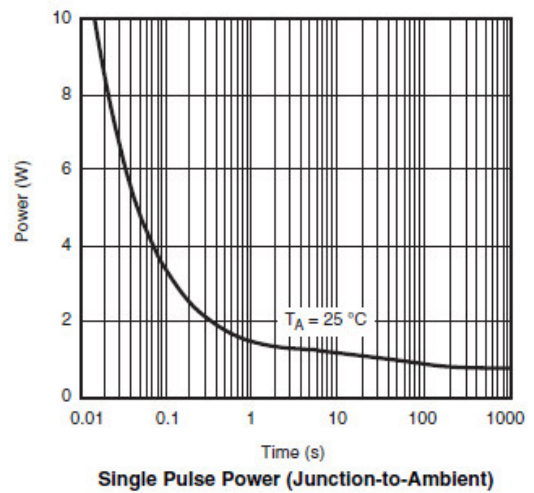
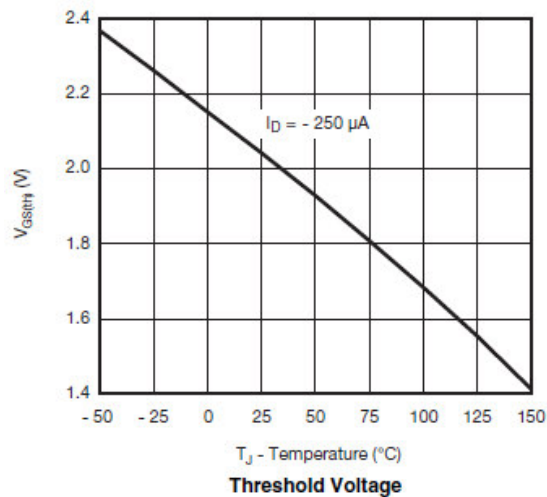
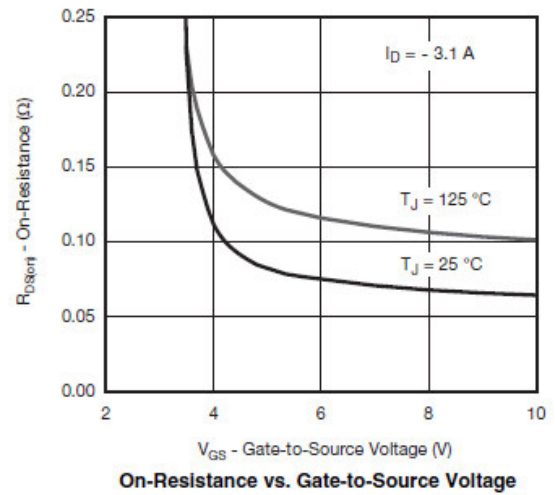
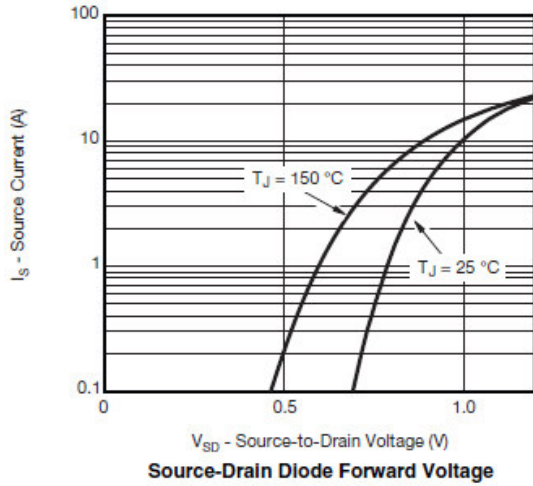
Single Pulse Power, Junction-to-Case



Safe Operating Area, Junction-to-Ambient



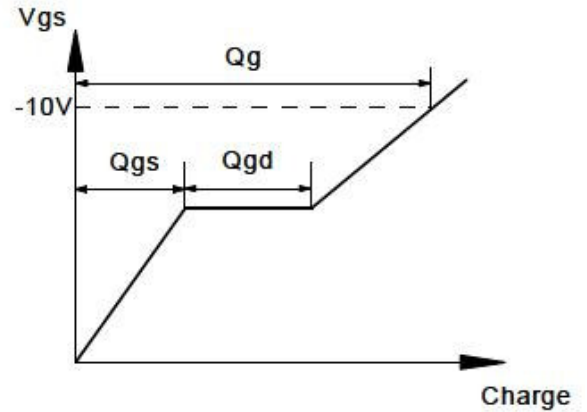
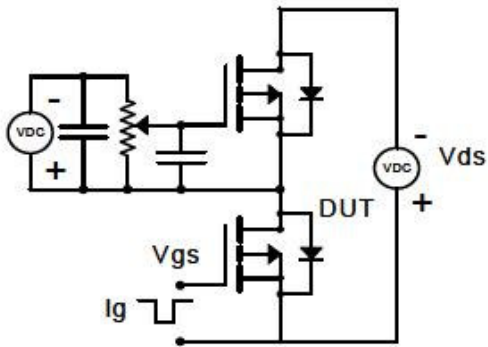
Typical Characteristics



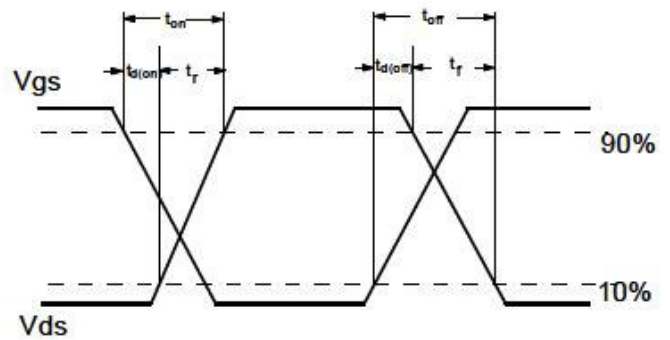
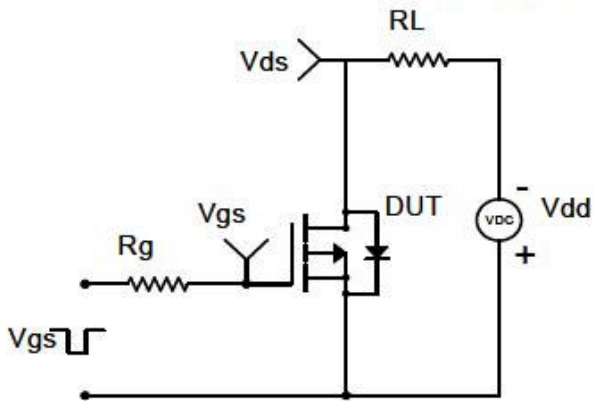


Typical Characteristics

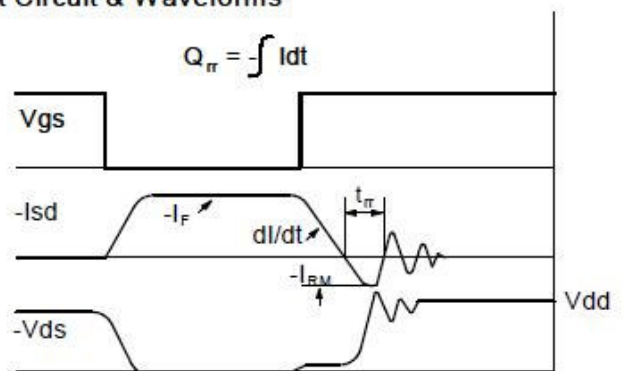
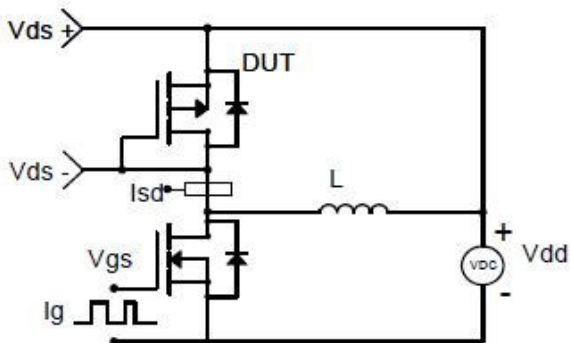
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

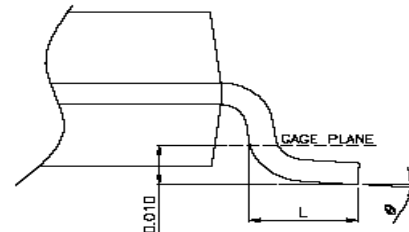
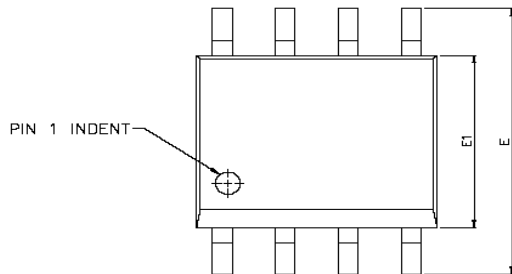


Diode Recovery Test Circuit & Waveforms

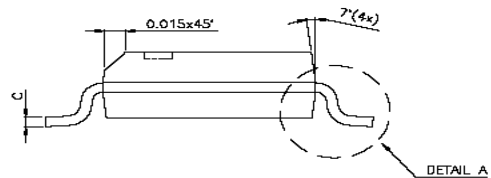
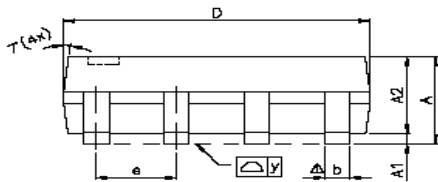




Package Information (SOP-8P)



DETAIL A



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.47	1.60	1.73	0.058	0.063	0.068
A1	0.10	—	0.25	0.004	—	0.010
A2	—	1.45	—	—	0.057	—
b	0.33	0.41	0.51	0.013	0.016	0.020
C	0.19	0.20	0.25	0.0075	0.008	0.0098
D	4.80	4.85	4.95	0.189	0.191	0.195
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e	—	1.27	—	—	0.050	—
L	0.38	0.71	1.27	0.015	0.028	0.050
Δ y	—	—	0.076	—	—	0.003
θ	0°	—	8°	0°	—	8°

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